

## PATENT ABSTRACTS OF JAPAN

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(71)Applicant : JAPAN SYNTHETIC RUBBER CO  
LTD

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(72)Inventor : CHIBA HIDEKI  
OKUBO JUNICHI  
NAITO MAKIKO  
SHIODA ATSUSHI**(54) FORMING METHOD OF RESIST PATTERN AND FORMING METHOD OF METALLIC PATTERN USING AFOREMENTIONED FORMING METHOD****(57)Abstract:**

**PURPOSE:** To provide a photo-resist pattern suitable for forming an evaporation bump and a lift-off process utilizing the photo-resist pattern.

**CONSTITUTION:** An alkali-soluble high-molecular material is used for a lower layer, and a two-layer resist layer employing an alkali developing negative type photo-resist composition containing (A) (a) an unsaturated carboxylic acid, (b) a radical polymerizable compound having an epoxy group, (c) a copolymer with other radical polymerizable compounds, (B) a polymerizable compound having at least one ethylene unsaturated double bond, and (C) a photopolymerization initiator is used for an upper layer, thus forming a resist pattern. A metal is evaporated, and the residual resist layer is lifted off together with an unnecessary metallic layer on the resist layer, thus forming a metallic pattern.

**LEGAL STATUS**

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